



SANYO Semiconductors

## DATA SHEET

# 6LN04MH — N-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- 1.5V drive.

### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		60	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		200	mA
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	800	mA
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	0.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0V	60			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =100μA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =100mA	280	480		mS
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =100mA, V <sub>GS</sub> =4V		2.2	2.9	Ω
	R <sub>DS(on)2</sub>	I <sub>D</sub> =50mA, V <sub>GS</sub> =2.5V		2.4	3.4	Ω
	R <sub>DS(on)3</sub>	I <sub>D</sub> =10mA, V <sub>GS</sub> =1.5V		3.5	7.0	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =20V, f=1MHz		26		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =20V, f=1MHz		5.9		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> =20V, f=1MHz		3.2		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		18.5		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		26		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		146		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		69		ns

Marking : FA

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TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

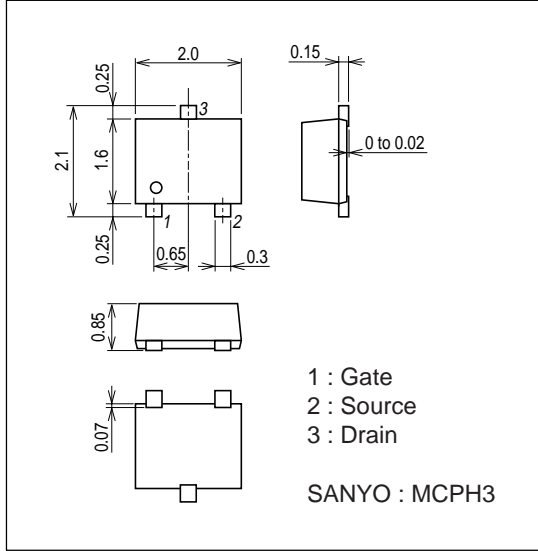
# 6LN04MH

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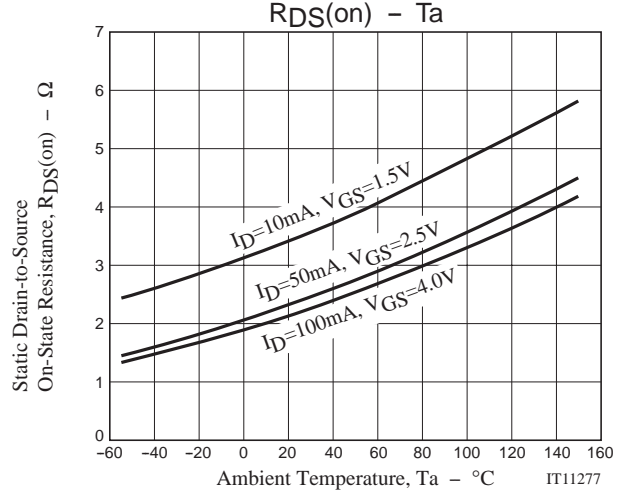
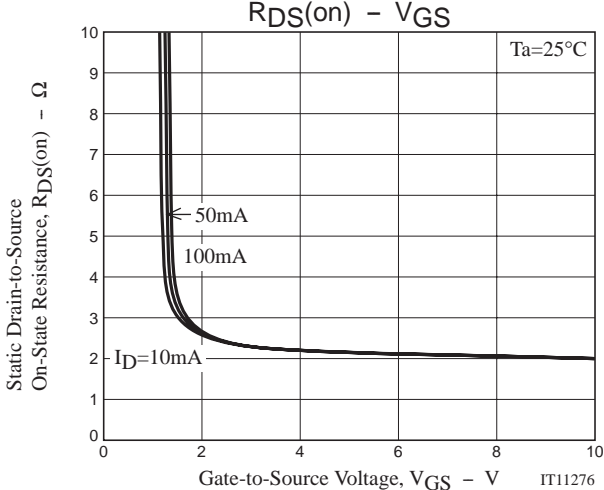
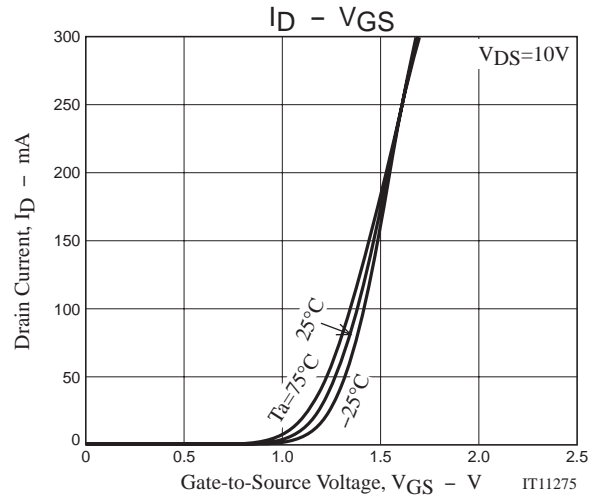
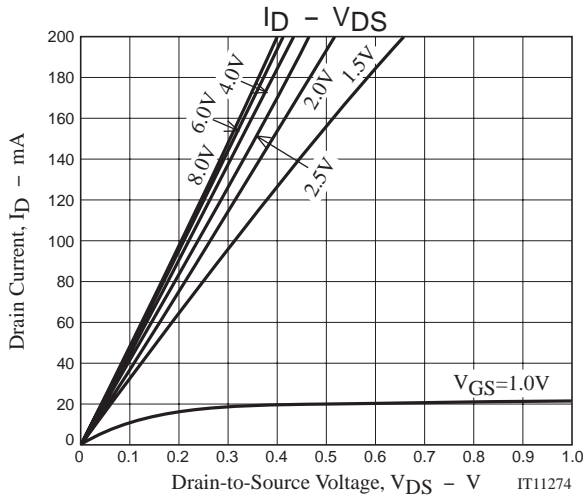
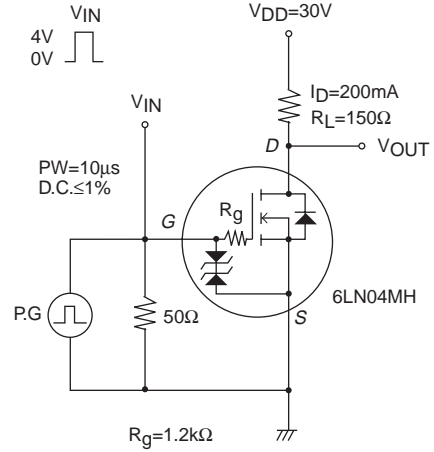
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V <sub>DS</sub> =30V, V <sub>GS</sub> =4V, I <sub>D</sub> =200mA		1.0		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =30V, V <sub>GS</sub> =4V, I <sub>D</sub> =200mA		0.2		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =30V, V <sub>GS</sub> =4V, I <sub>D</sub> =200mA		0.2		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =200mA, V <sub>GS</sub> =0V		0.83	1.2	V

## Package Dimensions

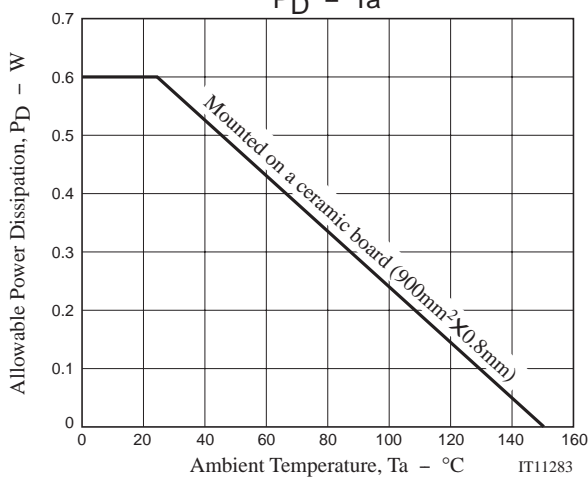
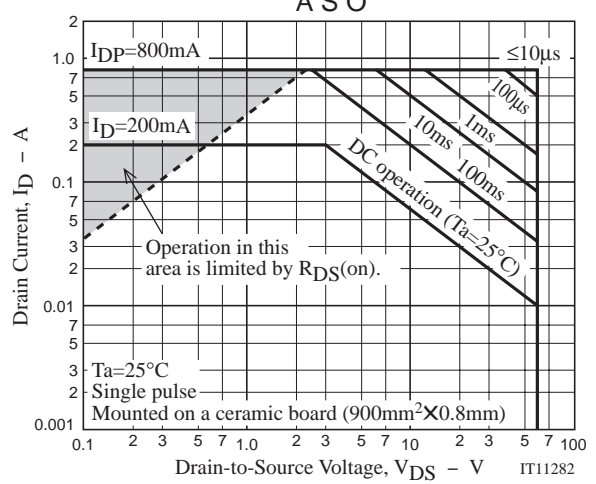
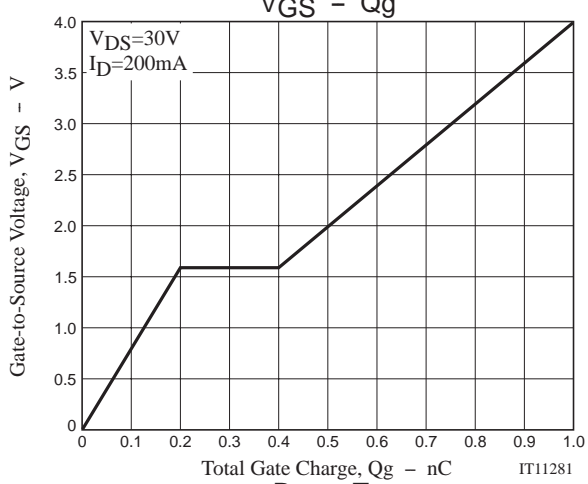
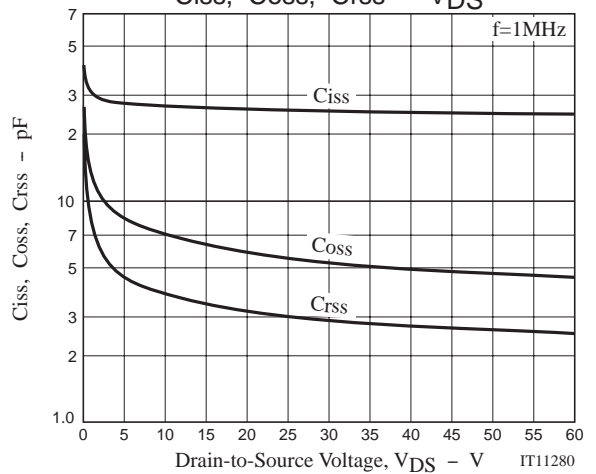
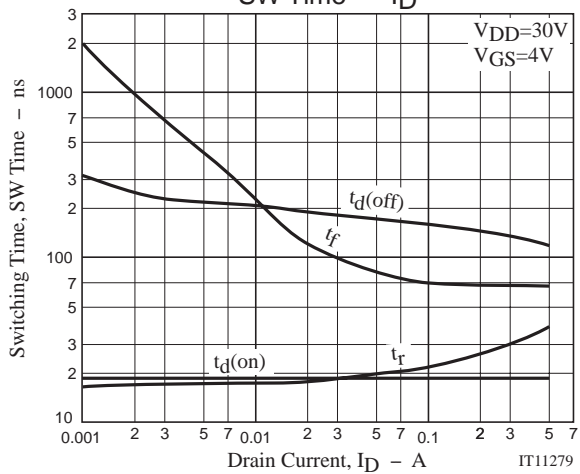
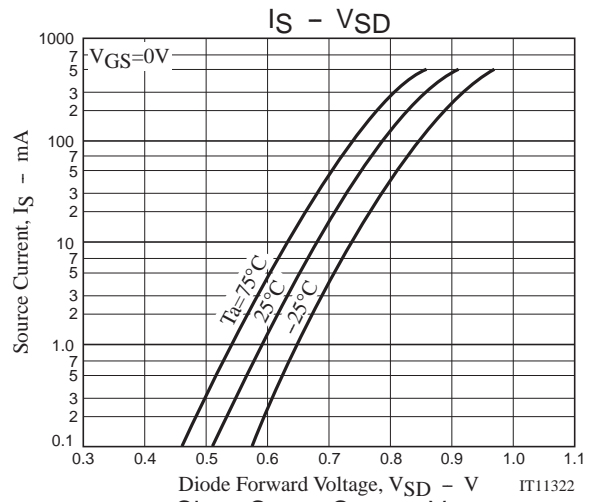
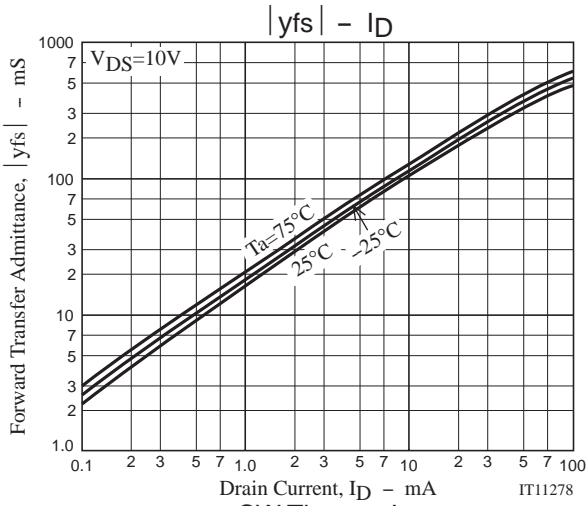
unit : mm (typ)  
7019A-003



## Switching Time Test Circuit



# 6LN04MH



Note on usage : Since the 6LN04MH is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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